

Product Overview

1N5817: 1.0 A, 20 V, Schottky Rectifier

For complete documentation, see the data sheet.

The Schottky Rectifier employs the Schottky Barrier principle in a large area metal-to-silicon power diode. The Schottky Rectifier's state-of-the-art geometry features chrome barrier metal, epitaxial construction with oxide passivation and metal overlap contact. It is ideally suited for use as rectifiers in low-voltage, high-frequency inverters, free wheeling diodes and polarity protection diodes.

Features

- Extremely Low v_F
- Low Stored Charge, Majority Carrier Conduction
- Low Power Loss/High Efficiency Mechanical Characteristics
- Case: Epoxy, Molded
- Weight: 0.4 gram (approximately)
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Shipped in plastic bags, 1000 per bag.
- Available Tape and Reeled, 5000 per reel, by adding a "RL" suffix to the part number
- Polarity: Cathode Indicated by Polarity Band
- Marking: 1N5817, 1N5818, 1N5819

For more features, see the data sheet

Part Electrical Specifications

Product	Pricing (\$/Unit)	Compliance	Status	Configuration	V_{RRM} Min (V)	V_F Max (V)	I_{RM} Max (μ A)	$I_{O(ree)}$ Max (A)	I_{FSM} Max (A)	t_r Max (ns)	C_j Max (pF)	Package Type
1N5817G	0.0827	Pb-free Halide free non AEC-Q and PPAP	Active	Single	20	0.45	1000	1	25	-	-	Axial Lead-2
1N5817RLG	0.0708	Pb-free Halide free non AEC-Q and PPAP	Active	Single	20	0.45	1000	1	25	-	-	Axial Lead-2

For more information please contact your local sales support at www.onsemi.com.

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